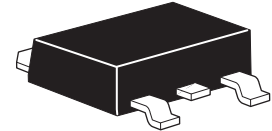


# ZXMP6A16K

## 60V DPAK P-channel enhancement mode MOSFET

### Summary

$V_{(BR)DSS}$	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)
-60	0.085 @ $V_{GS} = -10V$	8.2
	0.125 @ $V_{GS} = -4.5V$	6.75



### Description

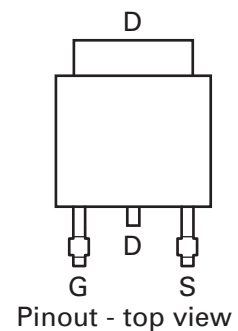
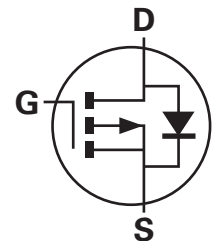
This new generation trench MOSFET from Zetex features a unique structure combining the benefits of low on-resistance and fast switching, making it ideal for high efficiency power management applications.

### Features

- Low on-resistance
- Fast switching speed
- Low threshold
- Low gate drive
- DPAK package

### Applications

- DC-DC converters
- Power management functions
- Disconnect switches
- Motor control



### Ordering information

Device	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMP6A16KTC	13	16	2500

### Device marking

ZXMP  
6A16

# ZXMP6A16K

## Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Drain-source voltage	$V_{DSS}$	-60	V
Gate-source voltage	$V_{GS}$	$\pm 20$	V
Continuous drain current @ $V_{GS} = 10V$ ; $T_{amb}=25^{\circ}C^{(b)}$ @ $V_{GS} = 10V$ ; $T_{amb}=70^{\circ}C^{(b)}$ @ $V_{GS} = 10V$ ; $T_{amb}=25^{\circ}C^{(a)}$	$I_D$	8.2 6.5 5.4	A
Pulsed drain current <sup>(c)</sup>	$I_{DM}$	27.2	A
Continuous source current (body diode) <sup>(b)</sup>	$I_S$	10	A
Pulsed source current (body diode) <sup>(c)</sup>	$I_{SM}$	27.2	A
Power dissipation at $T_{amb} = 25^{\circ}C^{(a)}$ Linear derating factor	$P_D$	4.24 33.9	W mW/ $^{\circ}C$
Power dissipation at $T_{amb} = 25^{\circ}C^{(b)}$ Linear derating factor	$P_D$	9.76 78	W mW/ $^{\circ}C$
Power dissipation at $T_{amb} = 25^{\circ}C^{(d)}$ Linear derating factor	$P_D$	2.11 16.8	W mW/ $^{\circ}C$
Operating and storage temperature range	$T_j, T_{stg}$	-55 to +150	$^{\circ}C$

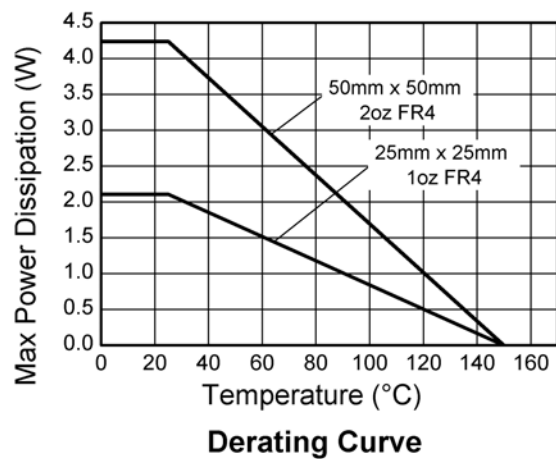
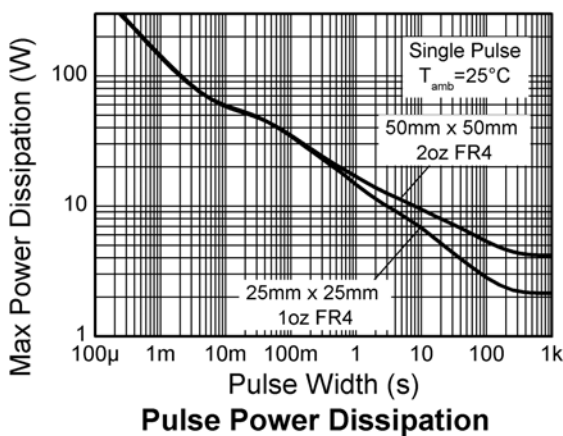
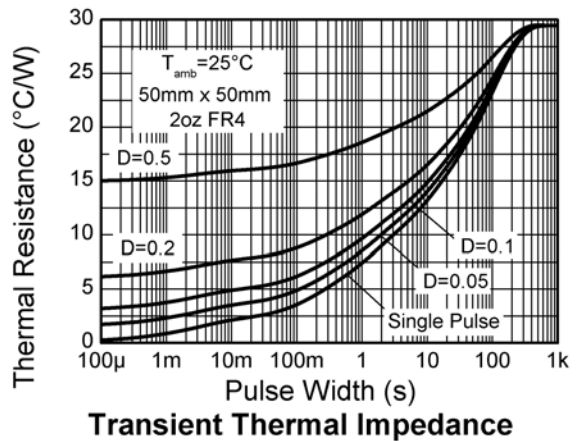
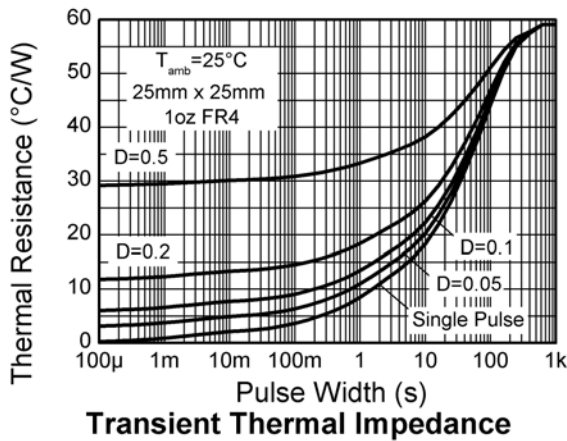
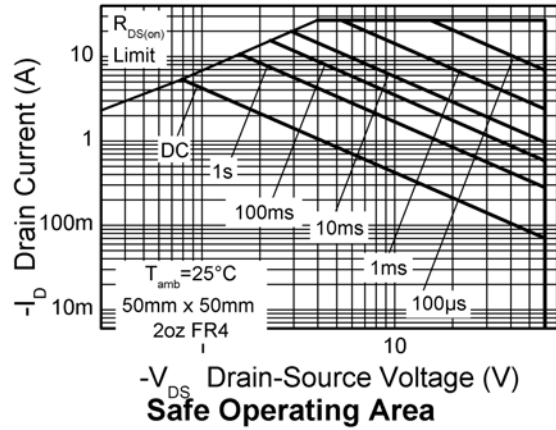
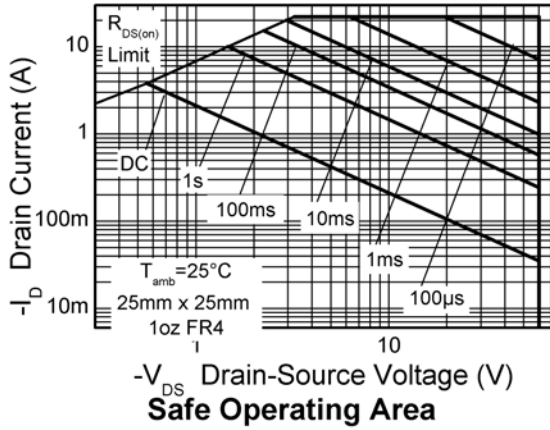
## Thermal resistance

Parameter	Symbol	Limit	Unit
Junction to ambient <sup>(a)</sup>	$R_{\theta JA}$	29.45	$^{\circ}C/W$
Junction to ambient <sup>(b)</sup>	$R_{\theta JA}$	12.8	$^{\circ}C/W$
Junction to ambient <sup>(d)</sup>	$R_{\theta JA}$	59.1	$^{\circ}C/W$

### NOTES:

- (a) For a device surface mounted on 50mm x 50mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions.
- (b) For a device surface mounted on FR4 PCB measured at  $t \leq 10$  sec.
- (c) Repetitive rating 50mm x 50mm x 1.6mm FR4 PCB,  $D=0.02$  pulse width=300 $\mu$ s - pulse width limited by maximum junction temperature.
- (d) For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

## Thermal characteristics



# ZXMP6A16K

## Electrical characteristics (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
<b>Static</b>						
Drain-source breakdown voltage	$V_{(BR)DSS}$	-60			V	$I_D = -250\mu\text{A}$ , $V_{GS} = 0\text{V}$
Zero gate voltage drain current	$I_{DSS}$			-1.0	$\mu\text{A}$	$V_{DS} = -60\text{V}$ , $V_{GS} = 0\text{V}$
Gate-body leakage	$I_{GSS}$			100	nA	$V_{GS} = \pm 20\text{V}$ , $V_{DS} = 0\text{V}$
Gate-source threshold voltage	$V_{GS(th)}$	-1.0			V	$I_D = -250\mu\text{A}$ , $V_{DS} = V_{GS}$
Static drain-source on-state resistance <sup>(*)</sup>	$R_{DS(on)}$			0.085	$\Omega$	$V_{GS} = -10\text{V}$ , $I_D = -2.9\text{A}$
				0.125	$\Omega$	$V_{GS} = -4.5\text{V}$ , $I_D = -2.4\text{A}$
Forward transconductance <sup>(*)</sup> (‡)	$g_{fs}$		7.2		S	$V_{DS} = -15\text{V}$ , $I_D = -2.9\text{A}$
<b>Dynamic</b> <sup>(‡)</sup>						
Input capacitance	$C_{iss}$		1021		pF	$V_{DS} = -30\text{V}$ , $V_{GS} = 0\text{V}$ $f = 1\text{MHz}$
Output capacitance	$C_{oss}$		83		pF	
Reverse transfer capacitance	$C_{rss}$		56		pF	
<b>Switching</b> (†) (‡)						
Turn-on-delay time	$t_{d(on)}$		3.5		ns	$V_{DD} = -30\text{V}$ , $I_D = -1\text{A}$ $R_G \approx 6.0\Omega$ , $V_{GS} = -10\text{V}$
Rise time	$t_r$		4.1		ns	
Turn-off delay time	$t_{d(off)}$		35		ns	
Fall time	$t_f$		10		ns	
Gate charge	$Q_g$		12.1		nC	$V_{DS} = -30\text{V}$ , $V_{GS} = -5\text{V}$ $I_D = -2.9\text{A}$
Total gate charge	$Q_g$		24.2		nC	$V_{DS} = -30\text{V}$ , $V_{GS} = -10\text{V}$ $I_D = -2.9\text{A}$
Gate-source charge	$Q_{gs}$		2.5		nC	
Gate drain charge	$Q_{gd}$		3.7		nC	
<b>Source-drain diode</b>						
Diode forward voltage <sup>(*)</sup>	$V_{SD}$		-0.85	-0.95	V	$T_j = 25^{\circ}\text{C}$ , $I_S = -3.4\text{A}$ , $V_{GS} = 0\text{V}$
Reverse recovery time <sup>(‡)</sup>	$t_{rr}$		29.2		ns	$T_j = 25^{\circ}\text{C}$ , $I_S = -2\text{A}$ , $di/dt = 100\text{A}/\mu\text{s}$
Reverse recovery charge <sup>(‡)</sup>	$Q_{rr}$		39.6		nC	

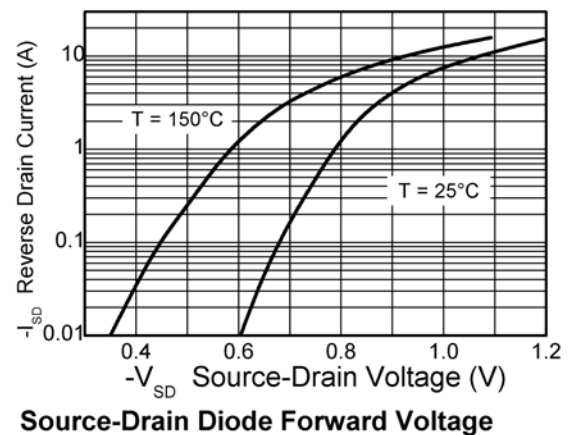
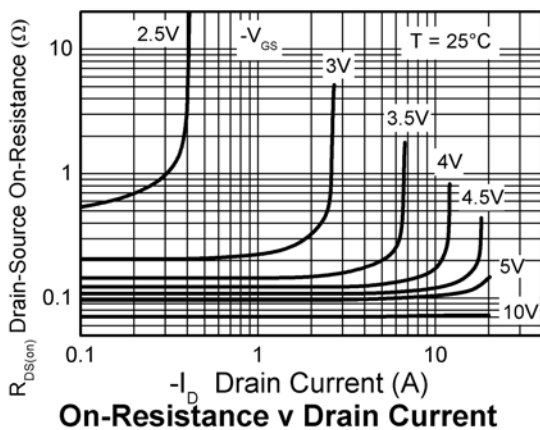
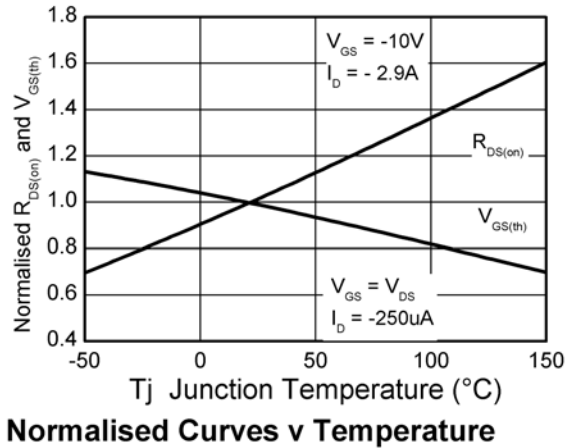
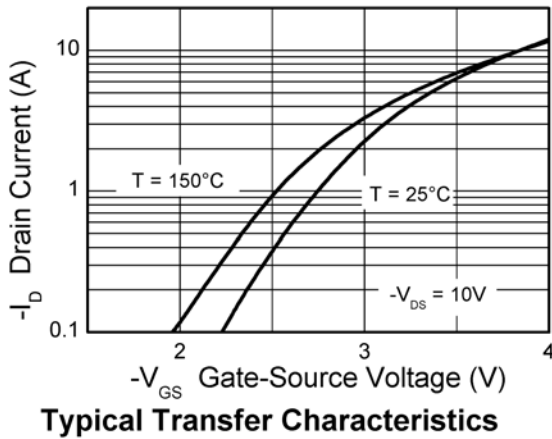
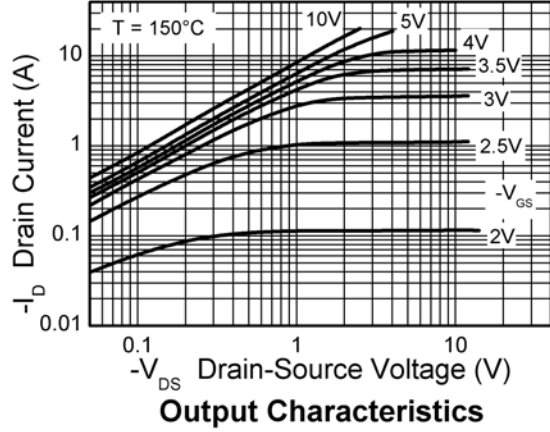
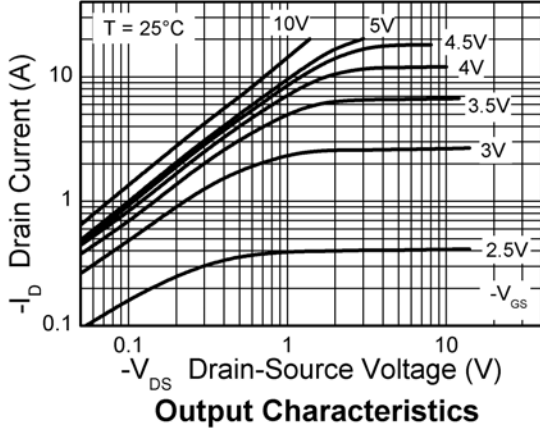
### NOTES:

(\*) Measured under pulsed conditions. Pulse width =  $300\mu\text{s}$ . Duty cycle  $\leq 2\%$ .

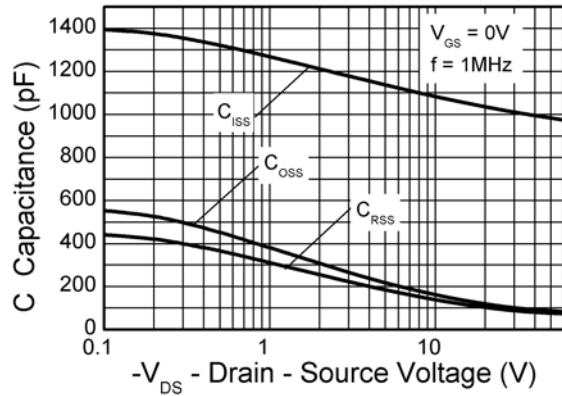
(†) Switching characteristics are independent of operating junction temperature.

(‡) For design aid only, not subject to production testing.

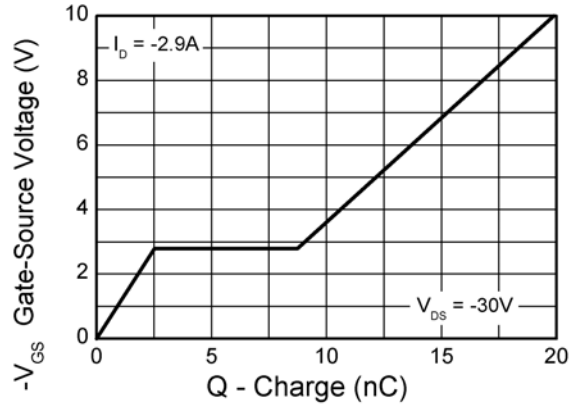
## Typical characteristics



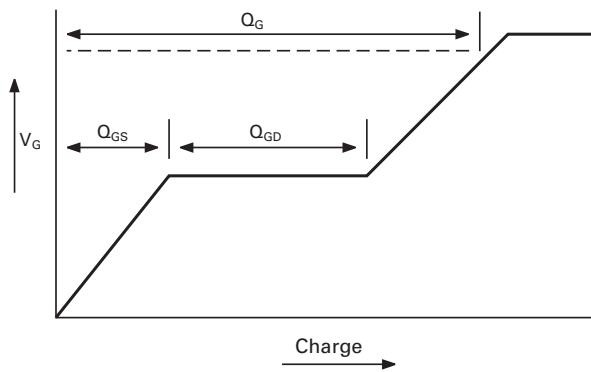
## Typical characteristics



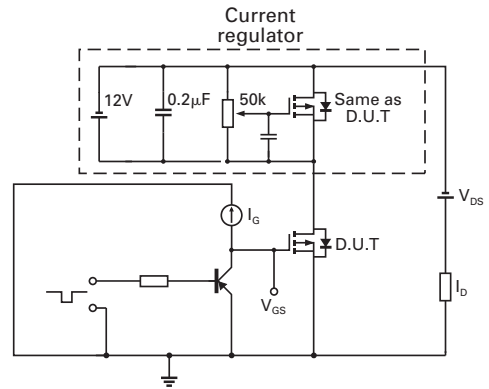
Capacitance v Drain-Source Voltage



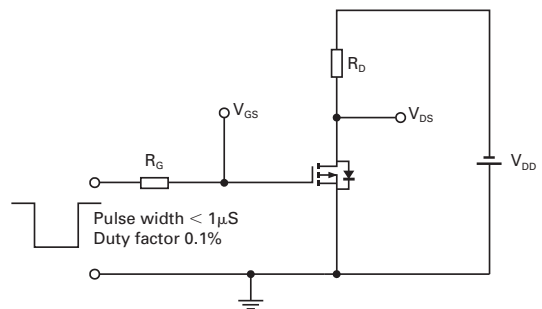
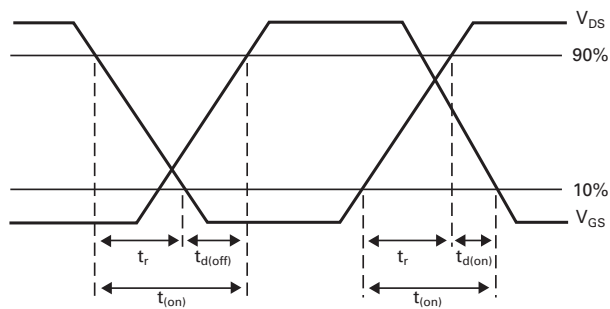
Gate-Source Voltage v Gate Charge



Basic gate charge waveform

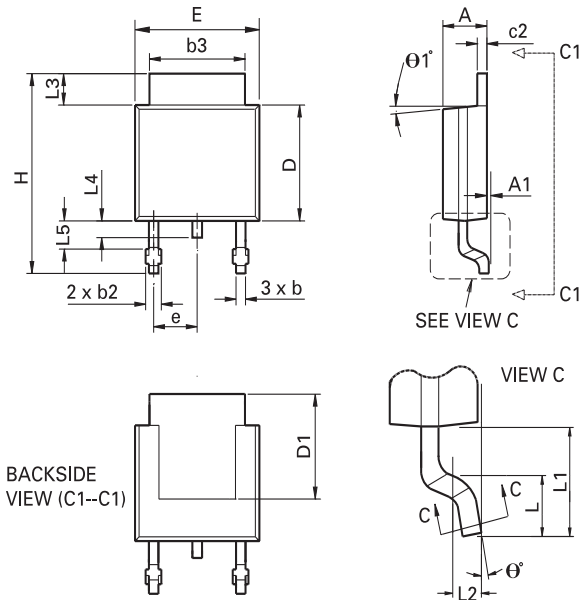


Gate charge test circuit



# ZXMP6A16K

## Package outline - DPAK



DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min	Max	Min	Max		Min	Max	Min	Max
A	0.086	0.094	2.18	2.39	e	0.090 BSC		2.29 BSC	
A1	-	0.005	-	0.127	H	0.370	0.410	9.40	10.41
b	0.020	0.035	0.508	0.89	L	0.055	0.070	1.40	1.78
b2	0.030	0.045	0.762	1.14	L1	0.108 REF		2.74 REF	
b3	0.205	0.215	5.21	5.46	L2	0.020 BSC		0.508 BSC	
c	0.018	0.024	0.457	0.61	L3	0.035	0.065	0.89	1.65
c2	0.018	0.023	0.457	0.584	L4	0.025	0.040	0.635	1.016
D	0.213	0.245	5.41	6.22	L5	0.045	0.060	1.14	1.52
D1	0.205	-	5.21	-	theta 1°	0°	10°	0°	10°
E	0.250	0.265	6.35	6.73	theta°	0°	15°	0°	15°
E1	0.170	-	4.32	-	-	-	-	-	-

**Note:** Controlling dimensions are in inches. Approximate dimensions are provided in millimeters

# ZXMP6A16K

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"Active"	Product status recommended for new designs
"Last time buy (LTB)"	Device will be discontinued and last time buy period and delivery is in effect
"Not recommended for new designs"	Device is still in production to support existing designs and production
"Obsolete"	Production has been discontinued

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Europe	Americas	Asia Pacific	Corporate Headquarters
Zetex GmbH Kustermann-park Balanstraße 59 D-81541 München Germany Telephone: (49) 89 45 49 49 0 Fax: (49) 89 45 49 49 49 europe.sales@zetex.com	Zetex Inc 700 Veterans Memorial Highway Hauppauge, NY 11788 USA Telephone: (1) 631 360 2222 Fax: (1) 631 360 8222 usa.sales@zetex.com	Zetex (Asia Ltd) 3701-04 Metroplaza Tower 1 Hing Fong Road, Kwai Fong Hong Kong Telephone: (852) 26100 611 Fax: (852) 24250 494 asia.sales@zetex.com	Zetex Semiconductors plc Zetex Technology Park, Chadderton Oldham, OL9 9LL United Kingdom Telephone: (44) 161 622 4444 Fax: (44) 161 622 4446 hq@zetex.com

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